Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("5660642").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 16:37
L2	1	("6506260").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 16:41
L3	1	("6799588").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 16:52
L4	1	JP-07066100-\$.did.	US-PGPUB; USPAT; USOCR; JPO	OR	ON	2007/12/13 16:55
L6	1	("4569695").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:04
L7	1	("5372651").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:04
L8	1	("6217665").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:04
L9	1	("6039815").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05
L10	1	("20030041876").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05
L11	1	("5763892").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05
L12	1	("6631726").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05
L13	1	("6003527").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05
L14	1	("6431184").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05
L15	1	("5975098").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:05

146		(112022040257011) PM				2007/42/42 42 04
L16	1	("20030192570").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/13 18:06
L17	17	("3849195" "4854337" "5464477" "5512106" "5762749" "5853489" "5894853" "5913980" "5989355" "5993739" "6033484" "6057240" "6123088" "6235122").PN. OR ("6506260").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/13 18:57
S1	6	moriguchi-yoshihiro.in.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:03
S2	. 1	izaki-ryo.in.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:04
S3	2	yasuike-yoshitomo.in.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:04
S4	1	kamaishi-takao.in.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:04
S5	7	ishida-takahisa.in.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:04
S6	1992	134/34.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:04
S7 ⁻	. 6	("4408400" "4779355" "5068977" "5147690" "5212877" "6158141").PN. OR ("6418640").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:13
S8	6165	(clean\$4 or dry\$4 or rins\$4 or treat\$4) same (air near2 knife)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:29
S9	53	"134"/\$.ccls. and ((water or "H. sub.2O" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:47
S10	530	((clean\$4 or dry\$4 or rins\$4 or treat\$4) same (air near2 knife)) same (substrate or wafer or semiconductor) same ((water or H2O or "H.sub.2O") and air)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 11:31

S11	10	((clean\$4 or dry\$4 or rins\$4 or treat\$4) same (air near2 knife)) same (substrate or wafer or semiconductor) same (heat\$4 near5 ((water or H2O or "H.sub. 2O") and air))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 17:35
S12	970	((water or "H.sub.2O" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 13:49
S13	6	("20040074601" "20050034742" "6062288" "6290865" "6444255" "6827814").PN. OR ("7119027").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 11:41
S14	64	"438"/\$.ccls. and ((water or "H. sub.2O" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 12:05
S15	2	"216"/92.ccls. and ((water or "H. sub.2O" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 12:05
S16	1	"438"/748,787.ccls. and ((water or "H.sub.20" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 12:05
S17	4	"134"/15.ccls. and ((water or "H. sub.2O" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 12:09
S20	1	("5601655").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/11 12:57
S21	1	("5524654").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/11 12:57
S22	33	"5601655"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 12:58
S23	5	"5524654"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/13 16:41

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S24	66	(heat\$4 near4 ((water or "H.sub. 20" or H2O) and air) and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR-	ON	2007/12/11 14:01
S25	297	156/345.11.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 14:35
S37	0	((((wash\$4 or rins\$4 or treatment\$4) near3 (water or H2O or "H.sub.2O")) and (dry\$4 near2 air)) near6 fill\$3) same (wafer or substrate or semiconductor) same (air near3 knife) same heat\$4	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 15:30
S38	0	((((wash\$4 or rins\$4 or treatment\$4) near3 (water or H2O or "H.sub.2O")) and (dry\$4 near2 air)) with fill\$3) same (wafer or substrate or semiconductor) same (air near3 knife) same heat\$4	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 15:31
S39	51	((((wash\$4 or rins\$4 or treatment\$4) near3 (water or H2O or "H.sub.2O")) and (dry\$4 near2 air)) with fill\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 15:34
S40	3810	(wafer or substrate or semiconductor) same (air near3 knife)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:31
S41	0	S40 and ((((wash\$4 or rins\$4 or treatment\$4) near3 (water or H2O or "H.sub.2O")) and (dry\$4 near2 air)) with fill\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 15:32
S43	720384	(wafer or semiconductor or substrate) and (roll\$3 or mov\$3 or conveyor\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:35
S44		S43 and (((fill near3 spac\$3) same (water or "H.sub.2O" or H2O)) and (air near3 knife))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:38
S45	40	S43 and (((fill near3 spac\$3) near4 (water or "H.sub.2O" or H2O)) and (air near3 knife))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:38

S46	37	S43 and (((fill near3 spac\$3) near4 (water or "H.sub.2O" or H2O)) and (air near3 knife)) and ((clean\$3 or rins\$3 or treat\$3 or wash\$3) and dry\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:41
S47	6990	((clean\$3 or rins\$3 or treat\$3 or wash\$3) and dry\$3) and (wafer or substrate or semiconductor) and (air near2 knife)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:41
S48	6499	S47 and (water or "H.sub.20" or H2O)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 15:42
S49	461	S48 and (heat\$4 near4 (air and (water or H2O or "H.sub.2O")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 16:01
S50	33131	(wafer or substrate or semiconductor) with (rollers)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 16:02
S51	8243	S50 and ((treat\$3 or rins\$3 or wash\$3) and dry\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 16:02
S52	59	S51 and ((heat\$3 near3 (water or H2O or "H.sub.2O")) and (heat\$3 near3 (air))) and (air near3 knife)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 16:05
S53	10	((clean\$4 or dry\$4 or rins\$4 or treat\$4) same (air near2 knife)) same (substrate or wafer or semiconductor) same ((heat\$4 near5 (water or H2O or "H.sub. 2O")) and (heat\$4 near5 air))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/11 16:37
S54	0	("10822498").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/11 16:37
S55	0	"10822498"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 16:37

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S56	1	("5878760").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/12/11 17:36
S57	11	"34"/\$.ccls. and ((water or "H.sub. 20" or H2O) and air and (air near2 knife) and ((mov\$3 or roll\$3) near2 (wafer or substrate or semiconductor)))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:49
S58	17732	(heat\$3 near3 (water or H2O or "H.sub.2O")) with evaporat\$3	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:51
S59	2402	S58 and (wafer or substrate or semiconductor)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:51
S60	1776	S59 and (wash\$3 or rins\$3 or treat\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:52
S61	1438	S60 and dry\$3	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:51
S62	305	(heat\$3 near3 (water or H2O or "H.sub.2O")) with (evaporat\$3 near3 (fast\$3 or increas\$3))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:51
S63	22	S62 and (wafer or substrate or semiconductor)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:51
S64	18	S63 and (wash\$3 or rins\$3 or treat\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/11 17:56